

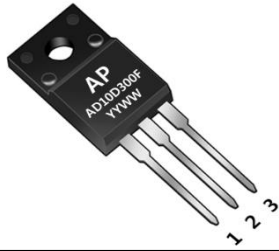
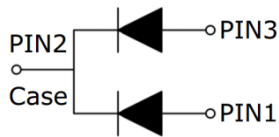
General Description

- ◇ The AD10D300 is trench MOS schottky diode with ultra low VF and low IR.
- These characteristics are optimized for efficiency, temperature and EMI performance.

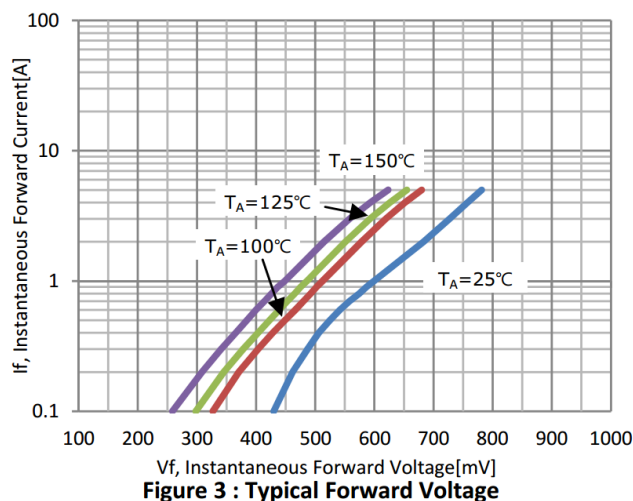
Electrical Characteristics

- ✓ Internal Diode : 2 die
- ✓ DC Blocking Voltage : 300V
- ✓ Average I_D per device : 5A
- ✓ Peak Forward Surge Current : 150A
- ✓ Typical Thermal Resistance : 4°C/W(TO220F)
- ✓ T_J and T_{STG} : -40 to 150°C
- ✓ Forward Voltage : 0.72V @ 2.5A, 25°C
0.77V @ 5A, 25°C
0.65V @ 5A, 125°C
- ✓ Reverse Current : Max 50uA @ 300V, 25°C

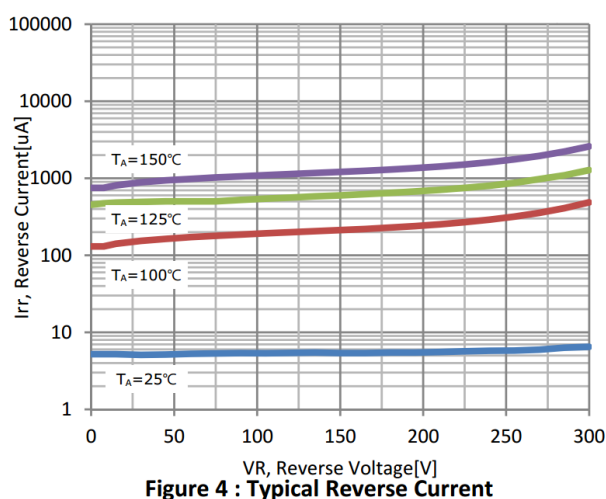
Package Information

Outline	
Diagram	

Forward Voltage

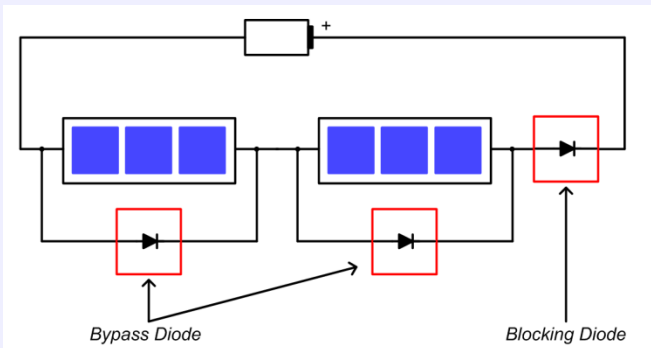


Reverse Current

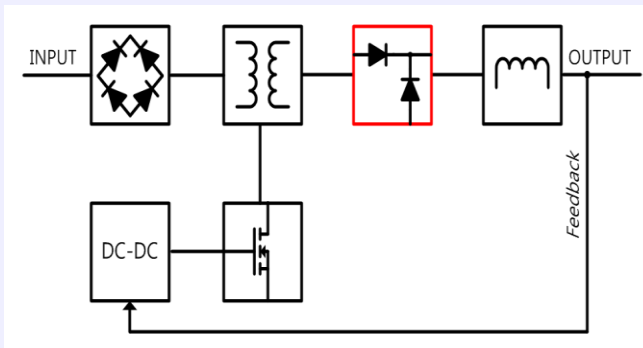


[DATASHEET LINK, APsemi Catalogue](#)

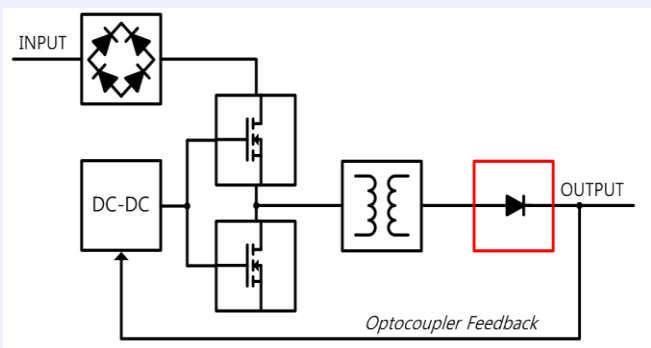
Solar Cell Junction Box



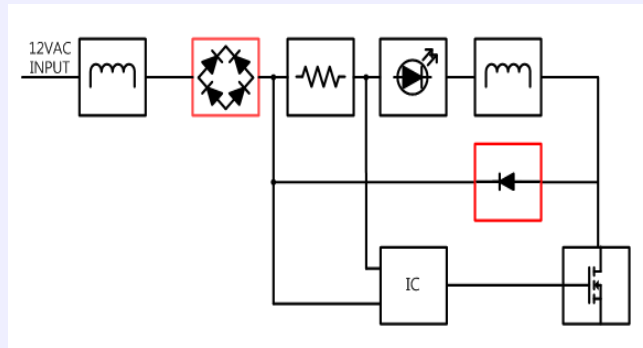
SMPS (Forward)



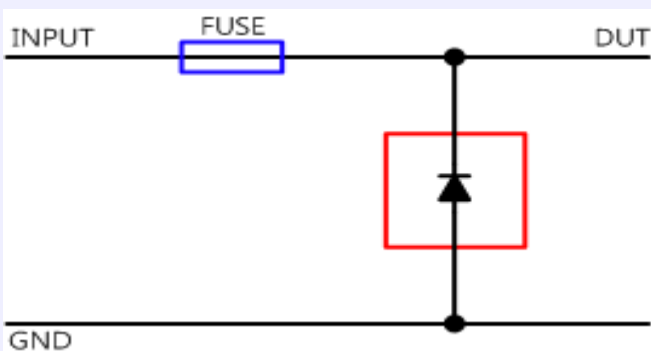
SMPS (Resonance)



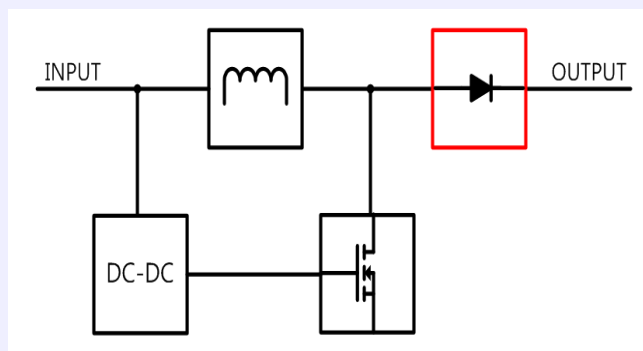
AC-DC (LED Lighting)



Reverse Protection Diode



PWM Boost Controller



Diode Line-up

I_{FAV}	Part No.	$V_R(V)$	$MaxV_{F@25^{\circ}C}(V)$	$Max I_R(\mu A)$	Package
3	AD360AF	60	0.51	25	SMAF/DO201AD
5	AD5100	100	TBD		SMAF
10	AD10D100	100	0.67	40	TO220F
	AD10D200	200	0.82	40	TO220F
	AD10D300	300	0.80	50	TO220F
	AD10S100	100	0.62	60	TO220F
	AD10U100	100	0.62	60	TO251/TO252
15	AD15S150	150	1.02	50	TO220F
	AD15U200	200	0.91	50	TO252
20	AD20D100	100	0.61	40	TO220F
	AD20D200	200	0.8	40	TO220F
	AD20S70	70	0.61	50	TO277
	AD20S100	100	0.71	40	TO220F
	AD20S150	150	0.93	40	TO220F
	AD2060T	60	0.57	40	TO277
30	AD30D100	100	0.68	30	TO220F
	AD30D200	200	0.9	40	TO220F
	AD30D200TF	200	0.86	40	TO247
40	AD40D60	60	0.65	40	TO220F
	AD40D100	100	0.75	30	TO220F
	AD40D100TF	100	0.71	50	TO247
	AD40D150	150	0.94	40	TO220F
	AD60D60TF	60	0.73	40	TO247